

Liangliang Zhang

List of Publications by Year in descending order

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Version: 2024-02-01

24
papers

552
citations

687363

13
h-index

713466

21
g-index

24
all docs

24
docs citations

24
times ranked

661
citing authors

#	ARTICLE	IF	CITATIONS
1	Analog/RF Performance of Si Nanowire MOSFETs and the Impact of Process Variation. IEEE Transactions on Electron Devices, 2007, 54, 1288-1294.	3.0	90
2	Experimental Investigations on Carrier Transport in Si Nanowire Transistors: Ballistic Efficiency and Apparent Mobility. IEEE Transactions on Electron Devices, 2008, 55, 2960-2967.	3.0	66
3	Selective Passivation of GeO ₂ /Ge Interface Defects in Atomic Layer Deposited High-k/i> MOS Structures. ACS Applied Materials & Interfaces, 2015, 7, 20499-20506.	8.0	66
4	Challenges of 22 nm and beyond CMOS technology. Science in China Series F: Information Sciences, 2009, 52, 1491-1533.	1.1	38
5	Interface Engineering for Atomic Layer Deposited Alumina Gate Dielectric on SiGe Substrates. ACS Applied Materials & Interfaces, 2016, 8, 19110-19118.	8.0	34
6	Pyrolysis and its mechanism of organomontmorillonite (OMMT) influenced by different functional groups. Journal of Thermal Analysis and Calorimetry, 2019, 137, 1-10.	3.6	30
7	Thermal behavior and flame retardancy of poplar wood impregnated with furfuryl alcohol catalyzed by boron/phosphorus compound system. Industrial Crops and Products, 2022, 176, 114361.	5.2	28
8	Montmorillonite-catalyzed furfurylated wood for flame retardancy. Fire Safety Journal, 2021, 121, 103297.	3.1	26
9	Border trap reduction in Al ₂ O ₃ /InGaAs gate stacks. Applied Physics Letters, 2015, 107, .	3.3	23
10	Characterization and analysis of gate-all-around Si nanowire transistors for extreme scaling. , 2011, , .		21
11	EOT Scaling of $\frac{m \text{TiO}_2}{m \text{Al}_2\text{O}_3}$ on Germanium pMOSFETs and Impact of Gate Metal Selection. IEEE Electron Device Letters, 2013, 34, 732-734.	3.9	21
12	Paraffin/wood flour/high-density polyethylene composites for thermal energy storage material in buildings: A morphology, thermal performance, and mechanical property study. Polymer Composites, 2018, 39, E1643.	4.6	21
13	Autonomous Last-Mile Delivery Vehicles in Complex Traffic Environments. Computer, 2020, 53, 26-35.	1.1	18
14	Interface Defect Hydrogen Depassivation and Capacitance-Voltage Hysteresis of Al ₂ O ₃ /InGaAs Gate Stacks. ACS Applied Materials & Interfaces, 2017, 9, 7819-7825.	8.0	13
15	Negative-Bias Temperature Instability in Gate-All-Around Silicon Nanowire MOSFETs: Characteristic Modeling and the Impact on Circuit Aging. IEEE Transactions on Electron Devices, 2010, 57, 3442-3450.	3.0	11
16	Interfacial Cation-Defect Charge Dipoles in Stacked TiO ₂ /Al ₂ O ₃ Gate Dielectrics. ACS Applied Materials & Interfaces, 2018, 10, 5140-5146.	8.0	10
17	HCl and NBTI induced degradation in gate-all-around silicon nanowire transistors. Microelectronics Reliability, 2011, 51, 1515-1520.	1.7	8
18	Electrochemical impedance spectroscopy for quantitative interface state characterization of planar and nanostructured semiconductor-dielectric interfaces. Nanotechnology, 2017, 28, 415704.	2.6	7

#	ARTICLE	IF	CITATIONS
19	Evolution of extractive composition in thermally modified Scots pine during artificial weathering. <i>Holzforschung</i> , 2019, 73, 747-755.	1.9	6
20	Combustion behavior of furfurylated wood in the presence of montmorillonite and its char characteristics. <i>Wood Science and Technology</i> , 2022, 56, 623-648.	3.2	6
21	Dimensional stability and decay resistance of clay treated, furfurylated, and clay-reinforced furfurylated poplar wood. <i>Holzforschung</i> , 2022, 76, 256-267.	1.9	4
22	Germanium Channel P-Mosfet with TiO ₂ /Al ₂ O ₃ Bilayer High-K Gate Stacks and Solutions for Metal/TiO ₂ Interface Stability. , 2012, , .		2
23	Motion planning in complex urban environments: An industrial application on autonomous last-mile delivery vehicles. <i>Journal of Field Robotics</i> , 2022, 39, 1258-1285.	6.0	2
24	A comprehensive study on Schottky barrier nanowire transistors (SB-NWTs): Principle, physical limits and parameter fluctuations. , 2008, , .		1